Docket No. 020494A

Divisional of U.S. Patent Application 10/117,219

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-26 (Canceled)

Claim 27 (Original): A method of making a thin-film piezo-resonator comprising steps of: preparing a substrate including a first surface and a second surface opposite to said first surface;

forming a resonator assembly which includes a first electrode held in contact with said first surface, a piezoelectric layer formed on the first electrode and a second electrode formed on the piezoelectric layer; and

forming a cavity by dry-etching the substrate, the cavity being disposed at a location corresponding to the resonator assembly, the cavity being opened in said first surface and said second surface;

wherein the cavity includes a side surface extending in a substantially perpendicular direction to said first surface.

Claim 28 (Original): The method according to Claim 27, wherein the dry etching is Deep-RIE.

Claim 29 (Original): The method according to Claim 27, further comprising the step of bonding a cover substrate to said second surface so as to close the cavity.

Claim 30 (Original): The method according to Claim 27, wherein a groove for dividing the substrate is also formed by etching at the cavity-forming step.

Claim 31 (Original): A method of making a thin-film piezo-resonator comprising steps of: preparing a substrate including a first surface and a second surface opposite to said first surface;

forming a resonator assembly which includes a first electrode held in contact with said first surface, a piezoelectric layer formed on the first electrode and a second electrode formed on the piezoelectric layer; and

forming a cavity by dry-etching the substrate, the cavity being disposed at a location corresponding to the resonator assembly, the cavity being opened in said first surface and said second surface;

wherein the first electrode and the piezoelectric layer are partially exposed to the cavity at the cavity-forming step.